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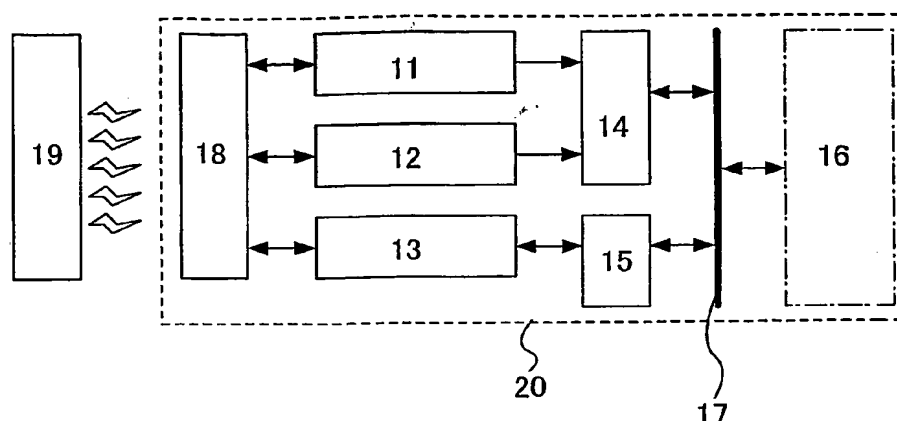
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(54) Title: SEMICONDUCTOR DEVICE AND DRIVING METHOD OF THE SAME



(57) Abstract: The invention provides a semiconductor device including a memory of a simple structure to provide an inexpensive semiconductor device and a driving method thereof. The semiconductor device of the invention includes a phase change memory including a memory cell array having a plurality of memory cells, a control circuit that controls the phase change memory, and an antenna. The memory cell array includes a plurality of bit lines that extend in a first direction and word lines that extend in a second direction perpendicular to the first direction. Each of the plurality of memory cells includes a phase change layer provided between the bit lines and the word lines. In the semiconductor device having the aforementioned structure, one or both of a conductive layer that forms the bit lines and a conductive layer that forms the word lines transmits light.

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